

FRED

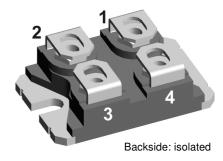
 V_{RRM} 600 V 96 A

35 ns

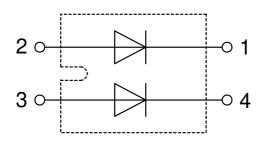
Fast Recovery Epitaxial Diode Low Loss and Soft Recovery Parallel legs

Part number

DSEI2x101-06A







Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~ • Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

20130703b

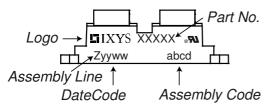


Fast Diode					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockii	ng voltage	$T_{VJ} = 25^{\circ}C$			600	V
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			600	V
IR	reverse current, drain current	$V_R = 600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			3	mA
		$V_R = 480 \text{ V}$	$T_{VJ} = 125^{\circ}C$			20	mΑ
V _F	forward voltage drop	I _F = 100 A	$T_{VJ} = 25^{\circ}C$			1.25	V
		$I_F = 200 \text{ A}$				1.40	٧
		I _F = 100 A	T _{VJ} = 150°C			1.17	٧
		$I_F = 200 \text{ A}$				1.70	٧
I FAV	average forward current	$T_{C} = 70^{\circ}C$	T _{VJ} = 150°C			96	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		$T_{VJ} = 150$ °C			0.70	٧
\mathbf{r}_{F}	slope resistance	ss calculation only				4.7	mΩ
R _{thJC}	thermal resistance junction to case)				0.5	K/W
R _{thCH}	thermal resistance case to heatsin	k			0.10		K/W
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			250	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			1.20	kA
CJ	junction capacitance	$V_R = 400 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		107		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		27		Α
		$I_F = 100 \text{ A}; V_R = 300 \text{ V}$	$T_{VJ} = 100^{\circ}C$		40		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 100 \text{ A; } V_R = 300 \text{ V} \\ -di_F / dt = 600 \text{ A/} \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}C$		80		ns
)		$T_{VJ} = 100^{\circ}C$		150		ns



Package SOT-227B (minibloc)			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					150	Α
T _{VJ}	virtual junction temperature	?			-40		150	°C
T _{op}	operation temperature			-40		125	°C	
T _{stg}	storage temperature			-40		150	°C	
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
$\mathbf{M}_{_{T}}$	terminal torque				1.1		1.5	Nm
d _{Spp/App}	araanaga diatanaa an aurfa	creepage distance on surface striking distance through air		10.5	3.2			mm
$d_{Spb/Apb}$	creepage distance on surra	ice Striking distance through an	terminal to backside 8.6		6.8			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		3000			٧
.002		t = 1 minute			2500			٧

Product Marking

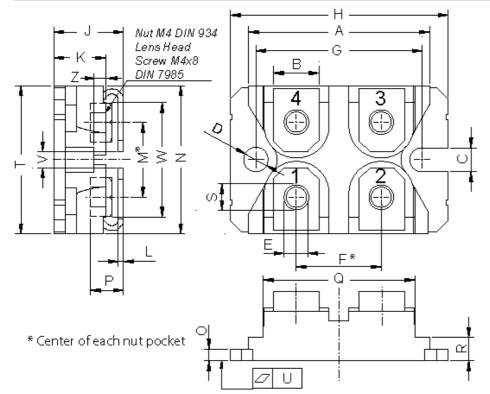


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI2x101-06A	DSEI2x101-06A	Tube	10	468029

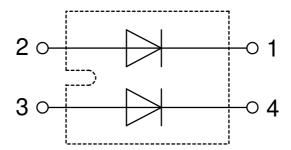
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$	R_0	Fast Diode		
V _{0 max}	threshold voltage	0.7		V
$R_{0 \; \text{max}}$	slope resistance *	3.5		$m\Omega$



Outlines SOT-227B (minibloc)



Dim.	Millir	neter	Inches	
DIIII.	min	max	min	max
Α	31.50	31.88	1.240	1.255
В	7.80	8.20	0.307	0.323
С	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
Е	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
Н	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
0	1.95	2.13	0.077	0.084
Р	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
Т	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106





Fast Diode

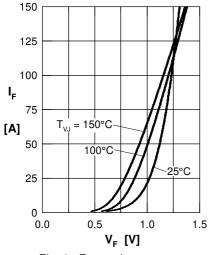


Fig. 1 Forward current I_F versus V_F

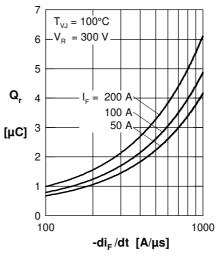


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_{F}/dt$

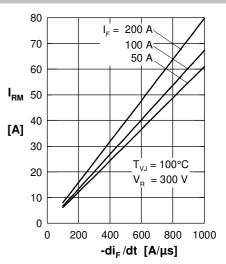


Fig. 3 Typ. peak reverse current I_{RM} versus -di_F/dt

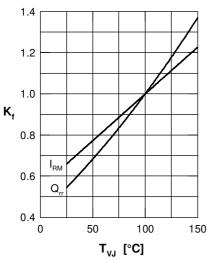


Fig. 4 Typ. dyn. parameters Q_r , I_{RM} versus T_{VJ}

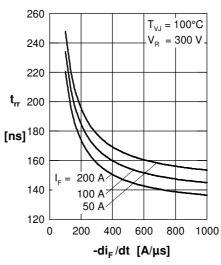


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

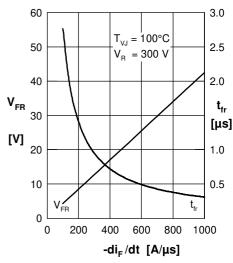


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

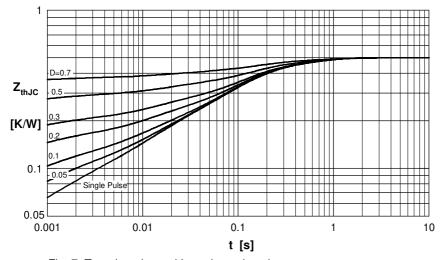


Fig. 7 Transient thermal impedance junction to case

Constants for $Z_{th,IC}$ calculation:

ı	H_{thi}	t _i
	[K/W]	[s]
1	0.020	0.00002
2	0.050	0.00081
3	0.076	0.01000
4	0.240	0.09400
5	0.114	0.45000

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Rectifiers category:

Click to view products by IXYS manufacturer:

Other Similar products are found below:

70HFR40 RL252-TP 150KR30A 1N5397 NTE5841 NTE6038 SCF5000 1N4002G 1N4005-TR JANS1N6640US 481235F
RRE02VS6SGTR 067907F MS306 70HF40 T85HFL60S02 US2JFL-TP A1N5404G-G ACGRA4007-HF ACGRB207-HF
CLH03(TE16L,Q) ACGRC307-HF ACEFC304-HF NTE6356 NTE6359 NTE6002 NTE6023 NTE6039 NTE6039 NTE6077 85HFR60 40HFR60
VS-88-7272PBF 70HF120 85HFR80 D126A45C SCF7500 D251N08B SCHJ22.5K SM100 SCPA2 SCH10000 SDHD5K VS12FL100S10 ACGRA4001-HF D1821SH45T PR D1251S45T NTE5990 NTE6358 NTE6162 NTE5850